2SD1890

Silicon NPN triple diffusion planar type Darlington

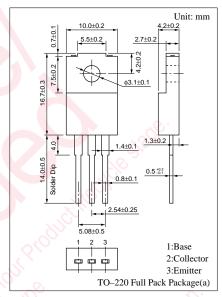
For power amplification Complementary to 2SB1250

Features

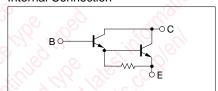
- Optimum for 25W HiFi output
- High foward current transfer ratio h_{FE}: 5000 to 30000
- Low collector to emitter saturation voltage V_{CE(sat)}: <2.5V
- Full-pack package which can be installed to the heat sink with one screw

Absolute Maximum Ratings (T_C=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	100	v
Collector to emitter voltage	V _{CEO}	80	V
Emitter to base voltage	V_{EBO}	5	V
Peak collector current	I_{CP}	6	A
Collector current	$I_{\rm C}$	3	A
Collector power T _C =25°C	D	35	11/0/1
dissipation Ta=25°C	P_{C}	2	W
Junction temperature	T_{j}	150	C. C.
Storage temperature	T _{stg}	-55 to +150	°C



Internal Connection



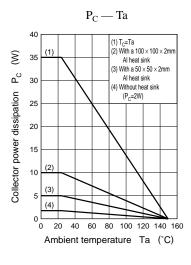
Electrical Characteristics (T_C=25°C)

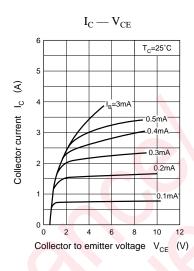
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 100V, I_E = 0$	10. S		100	μА
	I_{CEO}	$V_{CE} = 80V, I_{B} = 0$	0,		100	μА
Emitter cutoff current	I_{EBO}	$V_{EB} = 5V, I_C = 0$			100	μА
Collector to emitter voltage	V_{CEO}	$I_C = 30 \text{mA}, I_B = 0$	80			V
Forward current transfer ratio	h _{FE1}	$V_{CE} = 5V$, $I_C = 1A$	2000			
	h _{FE2} *	$V_{CE} = 5V, I_C = 2A$	5000		30000	
Collector to emitter saturation voltage	V _{CE(sat)}	$I_C = 2A$, $I_B = 2mA$			2.5	V
Base to emitter saturation voltage	V _{BE(sat)}	$I_C = 2A, I_B = 2mA$			3.0	V
Transition frequency	f_T	$V_{CE} = 10V, I_{C} = 0.5A, f = 1MHz$		20		MHz
Turn-on time	t _{on}	$I_C = 2A, I_{B1} = 2mA, I_{B2} = -2mA,$		3.5		μs
Storage time	t _{stg}			2.5		μs
Fall time	t _f	$V_{CC} = 50V$		0.6		μs

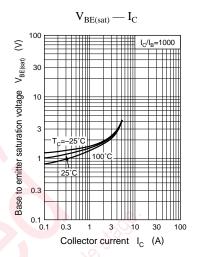
*h_{FE2} Rank classification

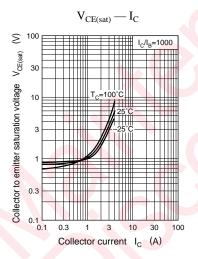
Rank	Q	P		
h _{FE2}	5000 to 15000	8000 to 30000		

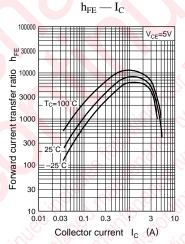
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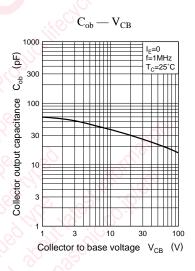


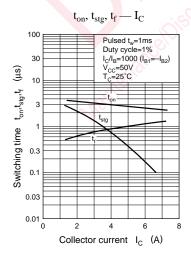




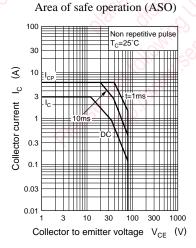






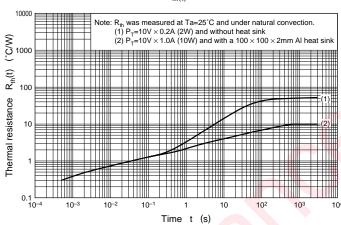


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Power Transistors 2SD1890





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